

# VBGL71505 Datasheet

## N-Channel 150V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ ) MAX.	$I_D$ (A)	$Q_g$ (TYP.)
150	0.005at $V_{GS}=10V$	160	75nC

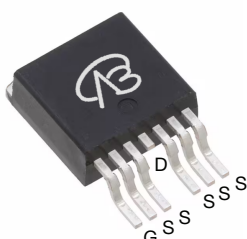
### FEATURES

- SGT technology Power MOSFET
- Maximum 150 °C junction temperature
- 100 %  $R_g$  and UIS tested

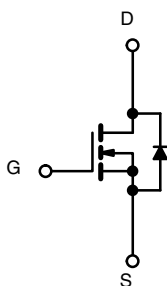


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

TO-263 7-Lead



Top View



N-Channel MOSFET

### APPLICATIONS

- Power supplies:
  - Uninterruptible power supplies
  - AC/DC switch-mode power supplies
  - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	150	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150\text{ }^{\circ}\text{C}$ )	$T_C = 25\text{ }^{\circ}\text{C}$	$I_D$	160	A
	$T_C = 70\text{ }^{\circ}\text{C}$		128	
Pulsed Drain Current ( $t = 100\text{ }\mu\text{s}$ )		$I_{DM}$	480	
Avalanche Current		$I_{AS}$	102	
Single Avalanche Energy <sup>a</sup>		$E_{AS}$	800	mJ
Maximum Power Dissipation <sup>a</sup>	$T_C = 25\text{ }^{\circ}\text{C}$	$P_D$	300 <sup>b</sup>	W
	$T_C = 100\text{ }^{\circ}\text{C}$		150 <sup>b</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +175	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) <sup>c</sup>		$R_{thJA}$	40	$^{\circ}\text{C/W}$
Junction-to-Case (Drain)		$R_{thJC}$	0.5	

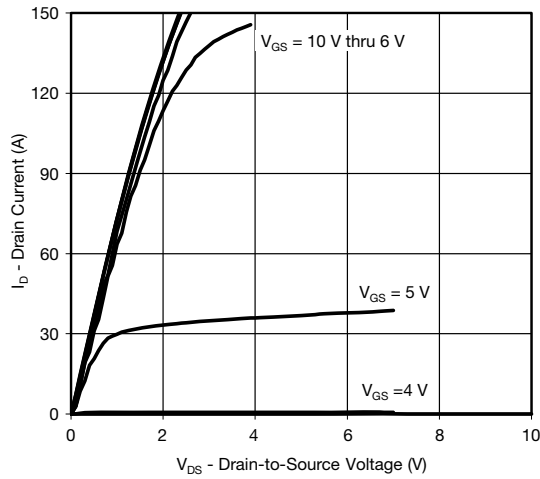
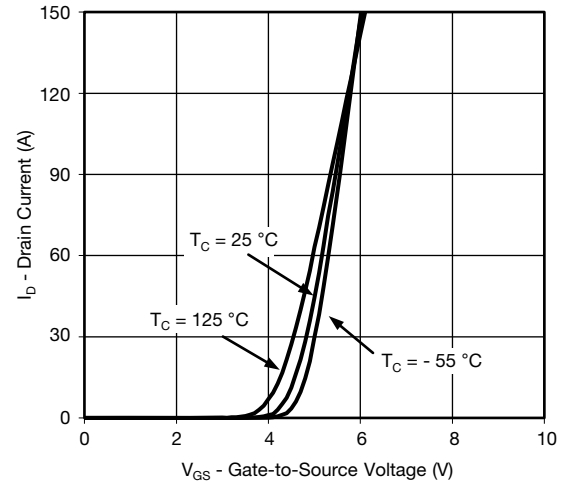
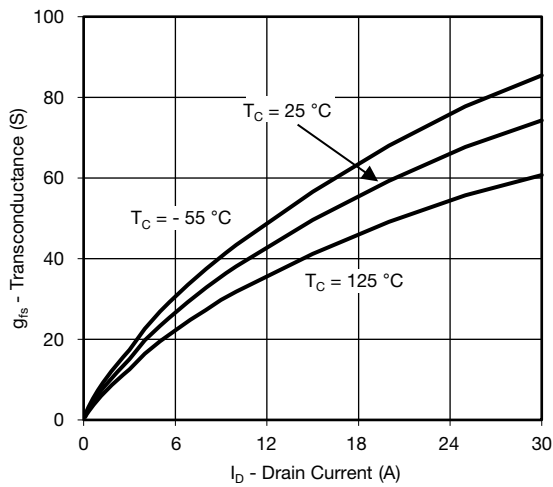
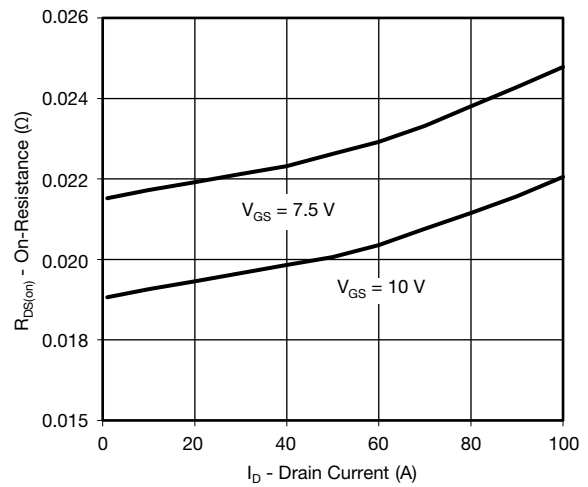
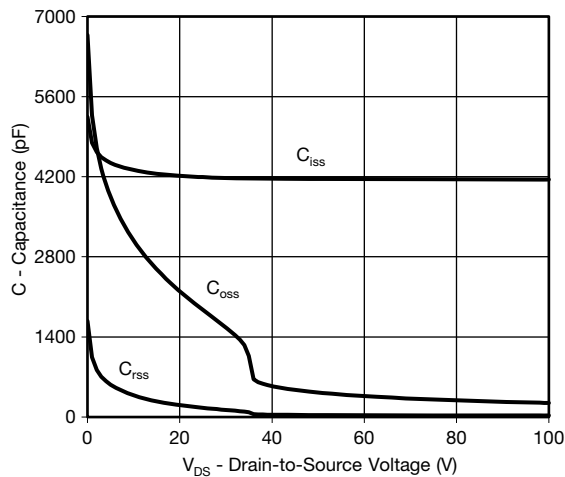
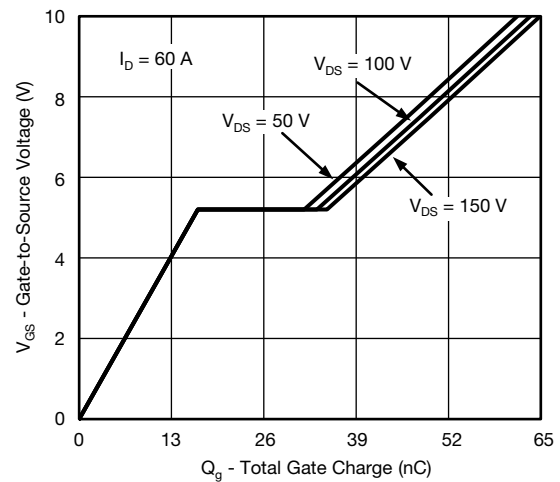
### Notes

- Duty cycle  $\leq 1\%$ .
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).

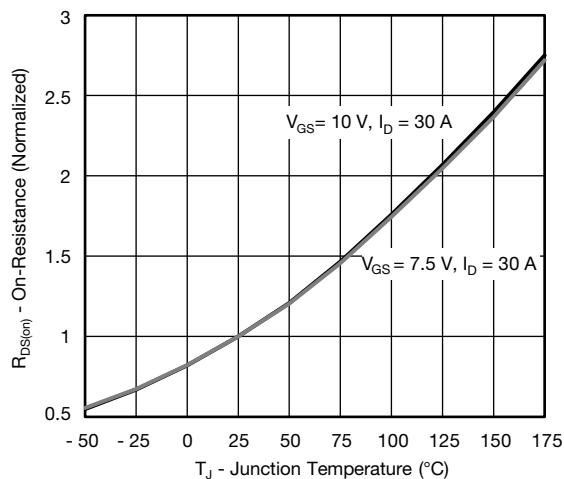
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	150	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.5	-	4.5	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 250	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	150	
		V <sub>DS</sub> = 120 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150°C	-	-	5	mA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 10 V, V <sub>GS</sub> = 10 V	90	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30 A	-	0.005	-	Ω
		V <sub>GS</sub> =4.5 V, I <sub>D</sub> = 20 A	-	0.008	-	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	-	75	-	S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V, f = 1 MHz	-	6500	-	pF
Output Capacitance	C <sub>oss</sub>		-	246	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	21	-	
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 60 A	-	75	80	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>		-	16.7	-	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	16.9	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	1.5	3	5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, R <sub>L</sub> = 1.66 Ω I <sub>D</sub> ≅ 60 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	15	25	ns
Rise Time <sup>c</sup>	t <sub>r</sub>		-	15	20	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		-	12	25	
Fall Time <sup>c</sup>	t <sub>f</sub>		-	10	18	
Drain-Source Body Diode Ratings and Characteristics <sup>b</sup> (T <sub>C</sub> = 25 °C)						
Pulsed Current (t = 100 μs)	I <sub>SM</sub>		-	-	480	A
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.8	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 30 A, di/dt = 100 A/μs	-	15	-	ns
Peak Reverse Recovery Charge	I <sub>RM(REC)</sub>		-	11	20	A
Reverse Recovery Charge	Q <sub>rr</sub>		-	0.9	1.8	μC

**Notes**

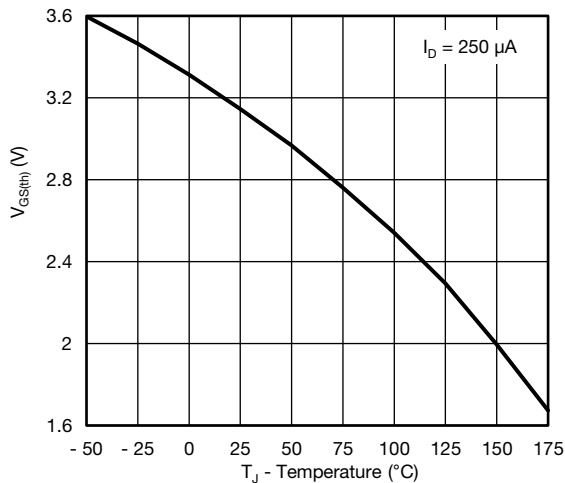
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.  
 c. Independent of operating temperature.

**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**Transconductance**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

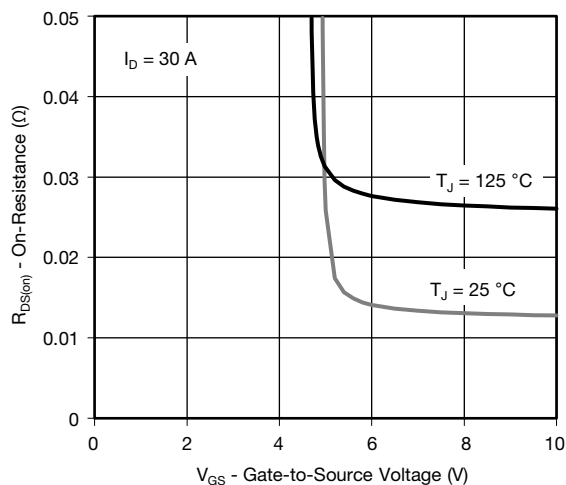
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)



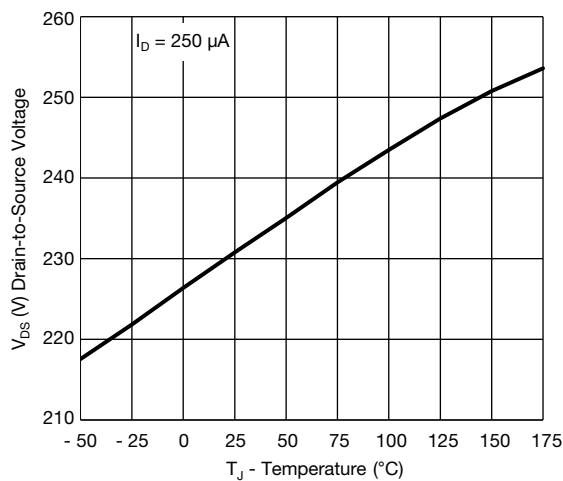
**On-Resistance vs. Junction Temperature**



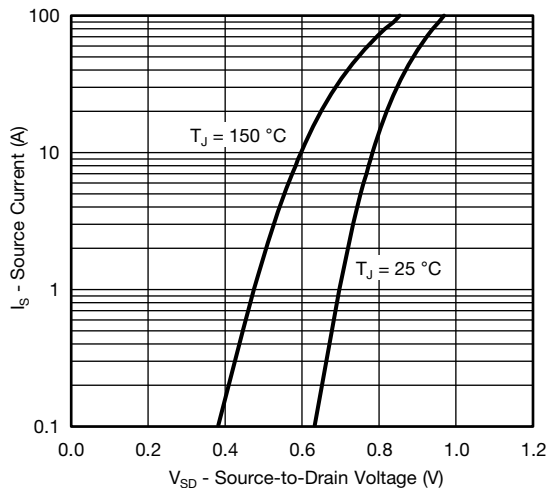
**Threshold Voltage**



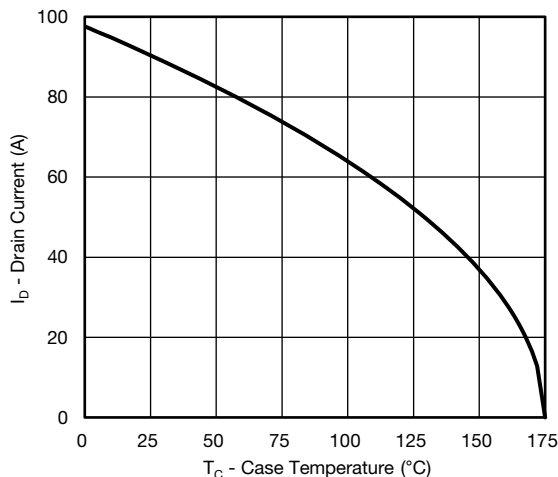
**On-Resistance vs. Gate-to-Source Voltage**



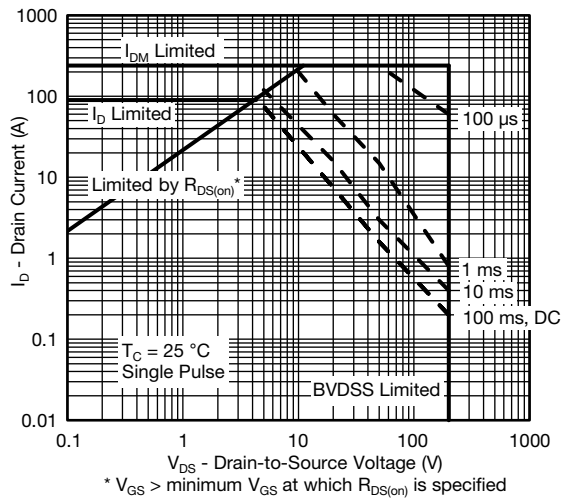
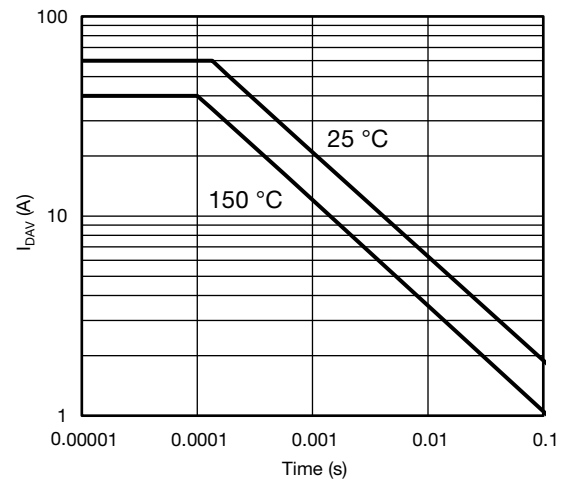
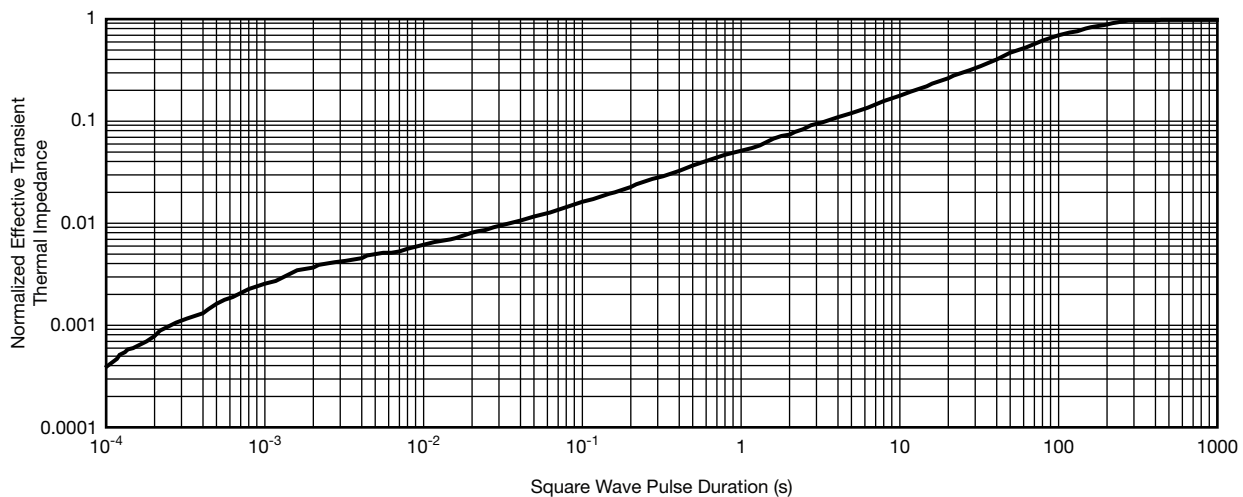
**Drain Source Breakdown vs. Junction Temperature**

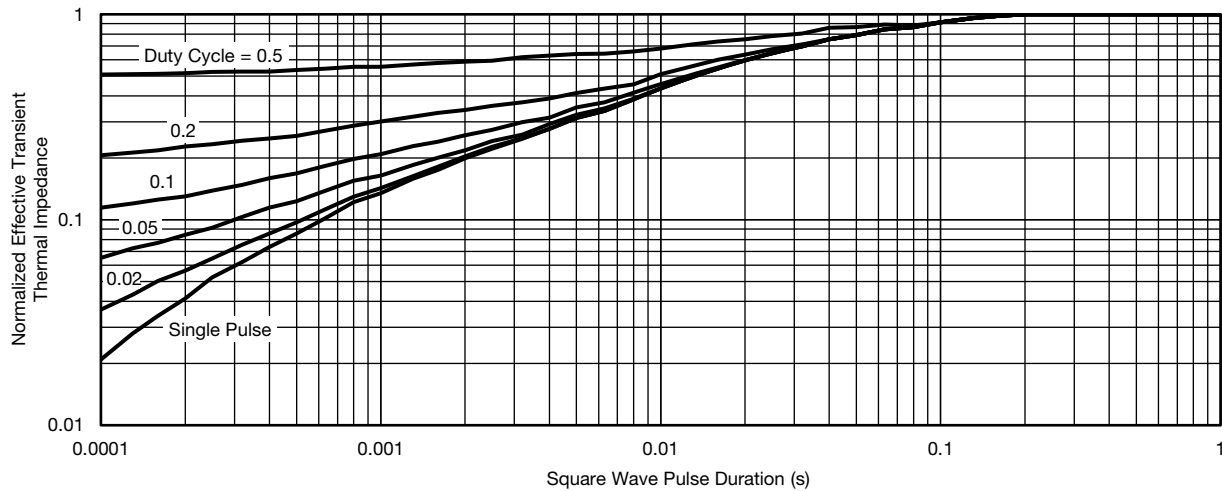


**Source Drain Diode Forward Voltage**



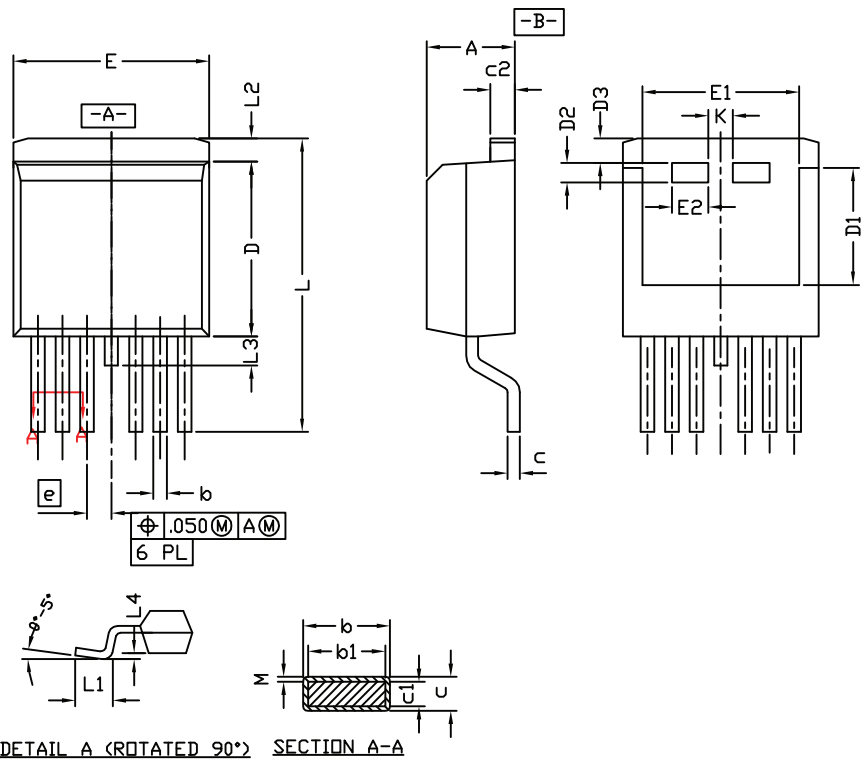
**Current De-rating**

**THERMAL RATINGS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

**Safe Operating Area**

**Single Pulse Avalanche Current Capability vs. Time**

**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**THERMAL RATINGS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Case****Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient ( $25\text{ }^{\circ}\text{C}$ )
  - Normalized Transient Thermal Impedance Junction to Case ( $25\text{ }^{\circ}\text{C}$ )are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

# D<sup>2</sup>PAK (TO-263-7L) Case Outline



## Notes

1. Plane B includes maximum features of heat sink tab and plastic.
2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
3. Pin to pin coplanarity max. 4 mils.
4. Lead thickness 25 mils.
5. For SUM part numbers lead thickness is 24 mils to 29 mils.
6. For reference only.
7. Use inches as the primary measurement.
8. This feature is only for SUM.

DIM.	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.160	0.190	4.064	4.826
b	0.020	0.039	0.508	0.990
b1	0.020	0.035	0.508	0.889
b2	0.045	0.055	1.143	1.397
c* SUB	0.012	0.018	0.305	0.457
c* SUM	0.022	0.028	0.559	0.711
c1	0.018	0.025	0.457	0.635
c2	0.045	0.055	1.143	1.397
D	0.340	0.380	8.636	9.652
D1	0.220	0.240	5.588	6.096
D2	0.038	0.042	0.965	1.067
D3	0.045	0.055	1.143	1.397
E	0.380	0.410	9.652	10.414
E1	0.245	-	6.223	-
E2	0.072	0.078	1.829	1.981
<b>[e]</b>	0.050 BSC		1.27 BSC	
K	0.045	0.055	1.143	1.397
L	0.575	0.625	14.605	15.875
L1	0.090	0.110	2.286	2.794
L2	0.040	0.055	1.016	1.397
L3	0.050	0.070	1.270	1.778
L4	0.010 BSC		0.254 BSC	
M	-	0.002	-	0.050

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